Electronic Structure, Surface Chemistry and Activity of La_{0.7}Sr_{0.3}MnO₃ Thin Film Cathodes at Elevated Temperatures

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Motivation and Objective

Oxygen reduction at cathode of solid oxide fuel cell is a key barrier to achieve higher power output and enable more economic functionality at intermediate temperatures.



The oxygen reduction reactivity depends on the electronic structure and surface chemistry driven by temperature, oxygen pressure, and lattice strain.

Goal - Identify the correlations of temperature, oxygen pressure, and strain to the electronic and chemical state and reactivity on the surface of epitaxially-grown $La_{0.7}Sr_{0.3}MnO_3$ thin films. In particular, focus on the Sr segregation, energy gap, and density of states (DOS) near E_{F}

Approach - In situ measurements to reveal the surface electronic structure and chemistry under the operating conditions of cathodes at elevated temperatures and oxygen pressures.





Surface electronic structure Scanning Tunneling Microscopy / Spectroscopy (STM/STS)

LSM/STO

(tensile)

Results: Strain effects

Surface structures



50 nm	o Height (5)	4 5 10 Dista
Compound	Lattice parameters	
¹ La _{0.7} Sr _{0.3} MnO ₃	a=b=c= 3.88 Å	
² SrO	a=b=c=5.16 Å	

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³ SrCO ₃	a=5.1, b=8.4, c=6.0 Å
⁴ La ₂ O ₃	a=b= 3.4, c=6.1 Å
⁵ (La,Sr) ₂ MnO ₄	a=b=3.84 , c=12.5 Å

Surface chemistry





15 20 25 ance (nm)

Both films show similar surface morphologies of a layer-by-layer structure with height difference of 4.0±0.3 Å.

→LSM perovskite itself is the most appropriate surface structure, no secondary phase on the surface.

Emission angle of 70° (surface sensitive)

Both films are larger than the bulk ratio of 0.3.

→ Sr-rich in near-surface region

→ The total Sr fraction on the A-site within the top surface is the same regardless of the sign or magnitude of strain.

Surface chemistry



Surface-Sr : under-coordinated Sr or Sr-OH on the perovskite. →More enrichment of surface-Sr driven by the tensile strain state in LSM/STO.

Electronic structures



(a) Tunneling spectra measured at RT in UHV (10⁻¹⁰ mbar).

(b) DFT calculations of total density states as a function of strain

(c) Tunneling spectra measured at 500 °C in 10-3 mbar of oxygen.

→ Tensile: @ RT, E_{g} large ; @ 500 °C, DOS_{EF} large, higher activity⁶.

Results: Temperature effects

Gap to no-gap transition



Reversible electronic structure transition from a semiconducting state to a metallic-like state between 400 °C and 500 °C in 10-5 mbar of oxygen.

No change in surface structure or step height difference.

Possible mechanisms: oxygen vacancy formation⁷, surface reconstruction⁸.

Conclusion

- ✓ Lattice strain: Sr-rich and larger band gap when tensile strained.
- Temperature: Transition from gap to no-gap in DOS at elevated temperature, higher DOS near E_F when tensile strained.
- These results demonstrate the important role of lattice strain and temperature in understanding and controlling the electronic structure and cation chemistry, and thus oxygen reduction activity of the cathode, for attaining higher power density in SOFCs.

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